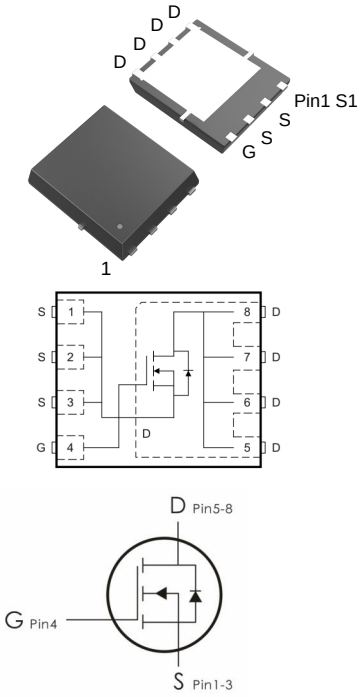
## Description：

This N-Channel MOSFET uses advanced SGT technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.




## Features：

1) $V_{DS}$=40V,$I_D$=160A,$R_{DS(ON)}$<1.6mΩ @$V_{GS}$=10V （Typ：1.3mΩ）
2) Low gate charge.
3) Green device available.
4) Advanced high cell denity SGT technology for ultra low $R_{DS(ON)}$.
5) Excellent package for good heat dissipation.
6) MSL3

## Package Marking and Ordering Information：

| Part NO. | Marking | Package | Packing |
|---|---|---|---|
| DON160N04T | 160N04T | DFN5*6-8-Clip | 5000 pcs/Reel |

## Absolute Maximum Ratings： ($T_C$=25℃ unless otherwise noted)

| Symbol | Parameter | Ratings | Units |
|---|---|---|---|
| $V_{DS}$ | Drain-Source Voltage | 40 | V |
| $V_{GS}$ | Gate-Source Voltage | ±20 | V |
| $I_D$ | Continuous Drain Current [1] | 160 | A |
| | Continuous Drain Current-$T_C$=100℃[1] | 112 | |
| $I_{DM}$ | Pulsed Drain Current [2] | 640 | |
| $P_D$ | Power Dissipation | 83 | W |
| $E_{AS}$ | Single pulse avalanche energy [3] | 200 | mJ |
| $T_J$, $T_{STG}$ | Operating and Storage Junction Temperature Range | -55-+150 | ℃ |

## Thermal Characteristics：

| Symbol | Parameter | Max | Units |
|---|---|---|---|
| $R_{\theta JC}$ | Thermal Resistance,Junction to Case | 1.5 | ℃/W |
| $R_{\theta JA}$ | Thermal Resistance,Junction to Ambient | 20 | ℃/W |

## Electrical Characteristics: ($T_C$=25℃ unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **Off Characteristics** | | | | | | |
| $BV_{DSS}$ | Drain-Sourtce Breakdown Voltage | $V_{GS}$=0V,$I_D$=250μA | 40 | --- | --- | V |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{GS}$=0V, $V_{DS}$=40V | --- | --- | 1 | μA |
| $I_{GSS}$ | Gate-Source Leakage Current | $V_{GS}$=±20V, $V_{DS}$=0A | --- | --- | ±100 | nA |
| **On Characteristics** | | | | | | |
| $V_{GS(th)}$ | Gate-Source Threshold Voltage | $V_{GS}$=$V_{DS}$, $I_D$=250μA | 1 | 1.6 | 2.5 | V |
| $R_{DS(ON)}$ | Drain-Source On Resistance[4] | $V_{GS}$=10V,$I_D$=20A | --- | 1.3 | 1.6 | mΩ |
| | | $V_{GS}$=4.5V,$I_D$=20A | --- | 1.8 | 2.4 | mΩ |
| **Dynamic Characteristics** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$=25V, $V_{GS}$=0V, f=1MHz | --- | 3200 | --- | pF |
| $C_{oss}$ | Output Capacitance | | --- | 2654 | -- | |
| $C_{rss}$ | Reverse Transfer Capacitance | | --- | 450.3 | --- | |
| **Switching Characteristics** | | | | | | |
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DS}$=20V,$R_{ENG}$=10Ω | --- | 848 | --- | ns |
| $t_r$ | Rise Time | | --- | 22.47 | --- | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | --- | 75 | --- | ns |
| $t_f$ | Fall Time | | --- | 36.2 | --- | ns |
| $Q_g$ | Total Gate Charge | $V_{DS}$=32V,$I_D$=10A | --- | 66 | --- | nC |
| $Q_{gs}$ | Gate-Source Charge | | --- | 14.28 | --- | nC |
| $Q_{gd}$ | Gate-Drain “Miller” Charge | | --- | 13.23 | --- | nC |
| **Drain-Source Diode Characteristics** | | | | | | |
| $V_{SD}$ | Diode Forward Voltage | $V_{GS}$=0V, $I_{SD}$=20A | --- | --- | 0.78 | V |
| $I_S$ | Continuous Drain Curren | VD=VG=0V | --- | --- | 160 | A |
| $I_{SM}$ | Pulsed Drain Current | | --- | --- | 640 | A |
| Trr | Reverse Recovery Time | $I_F$=1A,$T_J$=25℃ | --- | 31 | --- | ns |
| Qrr | Reverse Recovery Charge | dI/dt=100A/us | --- | 110 | --- | nC |

## Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. EAS condition : TJ=25℃,VDD=20V,$V_G$=10V,L=0.1mH
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

## Typical Characteristics: ($T_C$=25℃ unless otherwise noted)

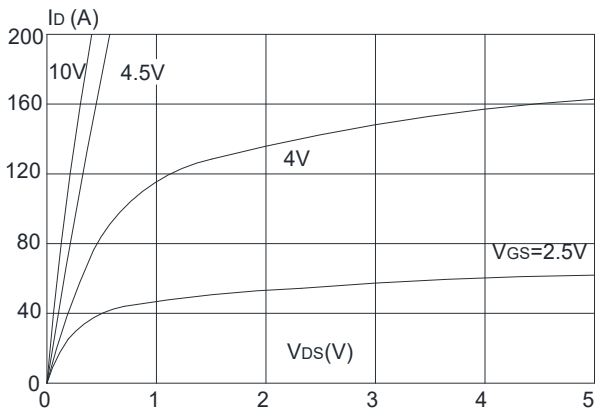



**Figure1:** Output Characteristics

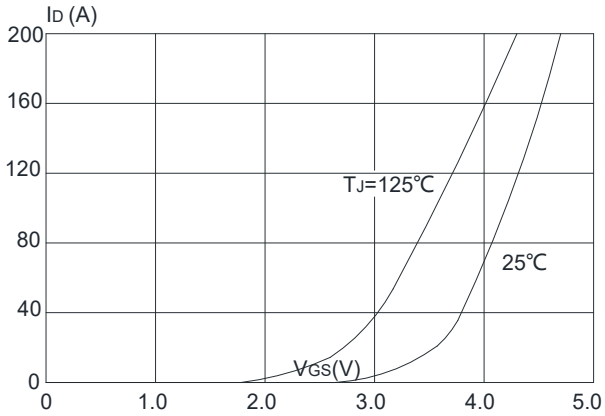



**Figure 2:** Typical Transfer Characteristics

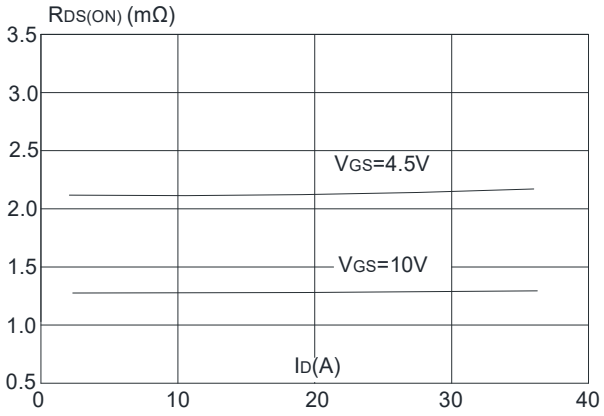



**Figure 3:**On-resistance vs. Drain Current

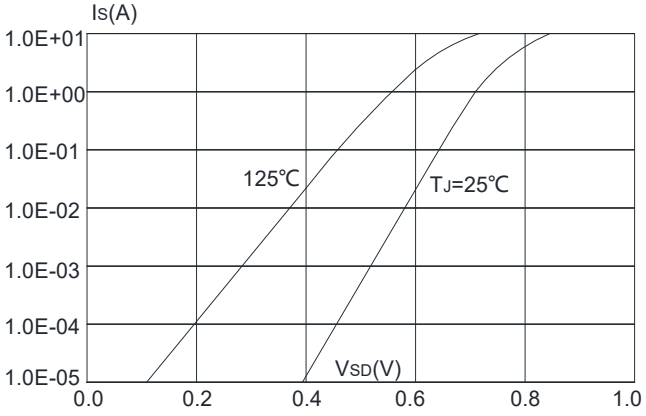



**Figure 4**: Body Diode Characteristics

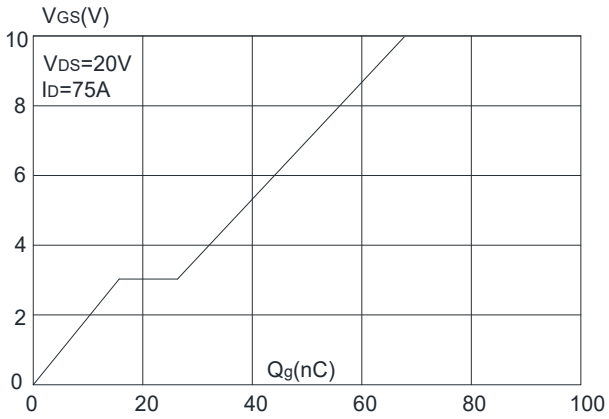



**Figure 5:** Gate Charge Characteristics

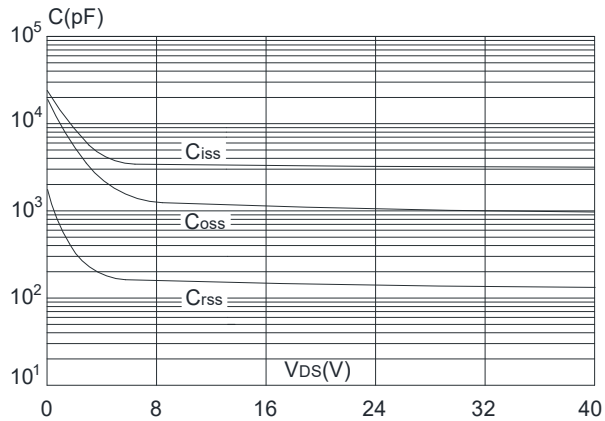



**Figure 6:** Capacitance Characteristics

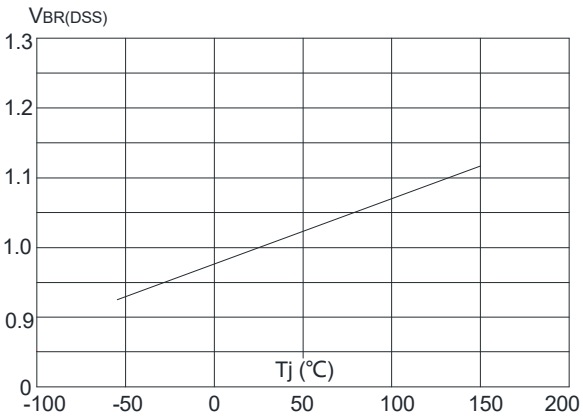



**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature

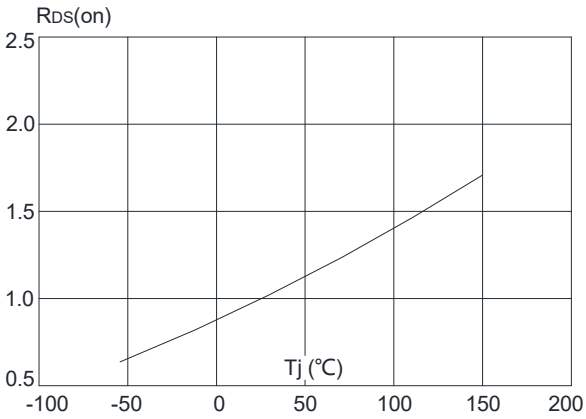



**Figure 8:** Normalized on Resistance vs. Junction Temperature

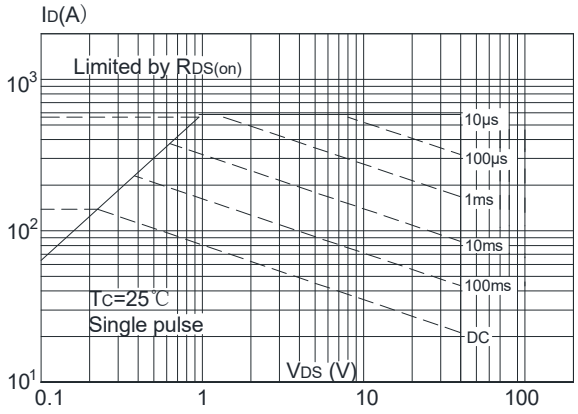



**Figure 9:** Maximum Safe Operating Area

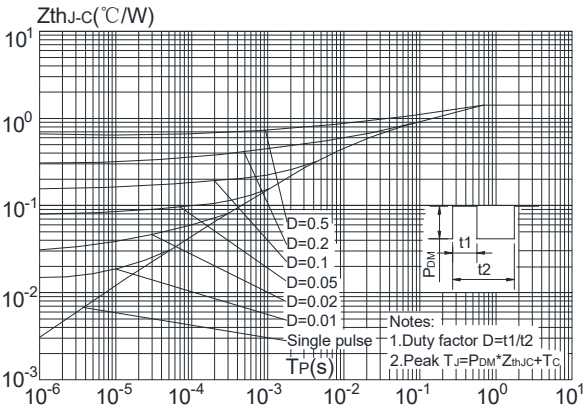
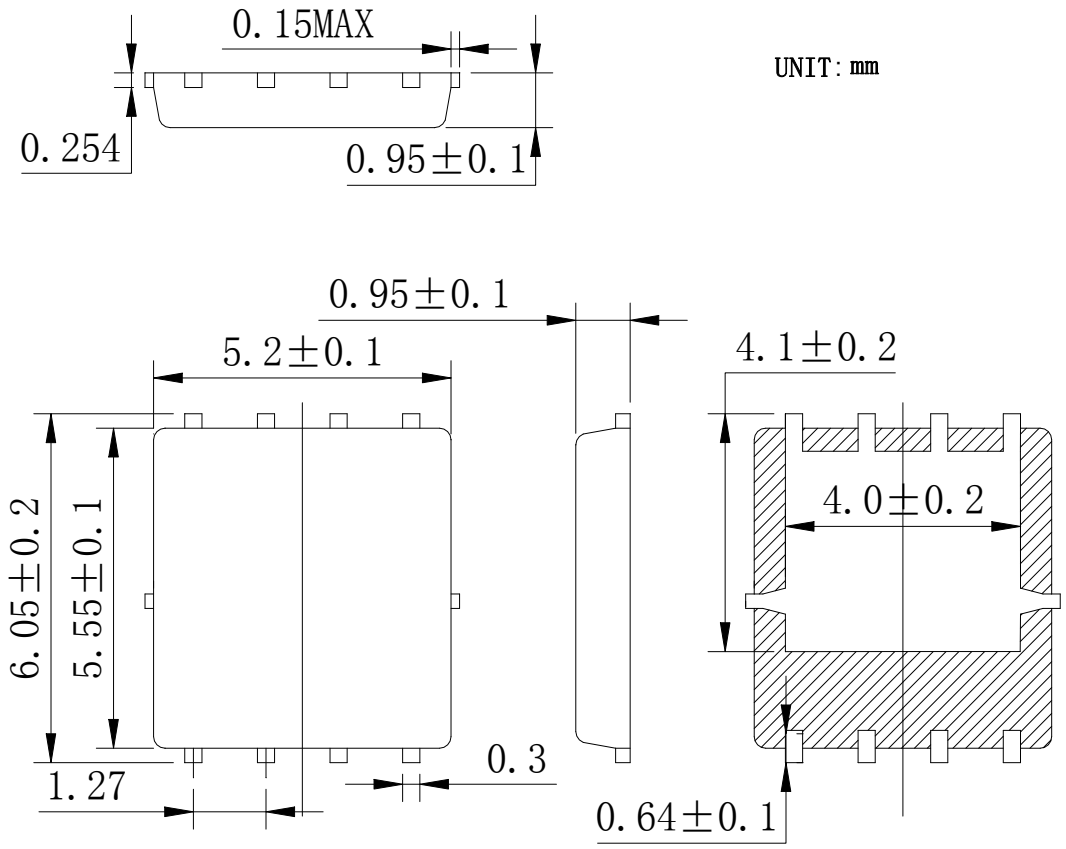


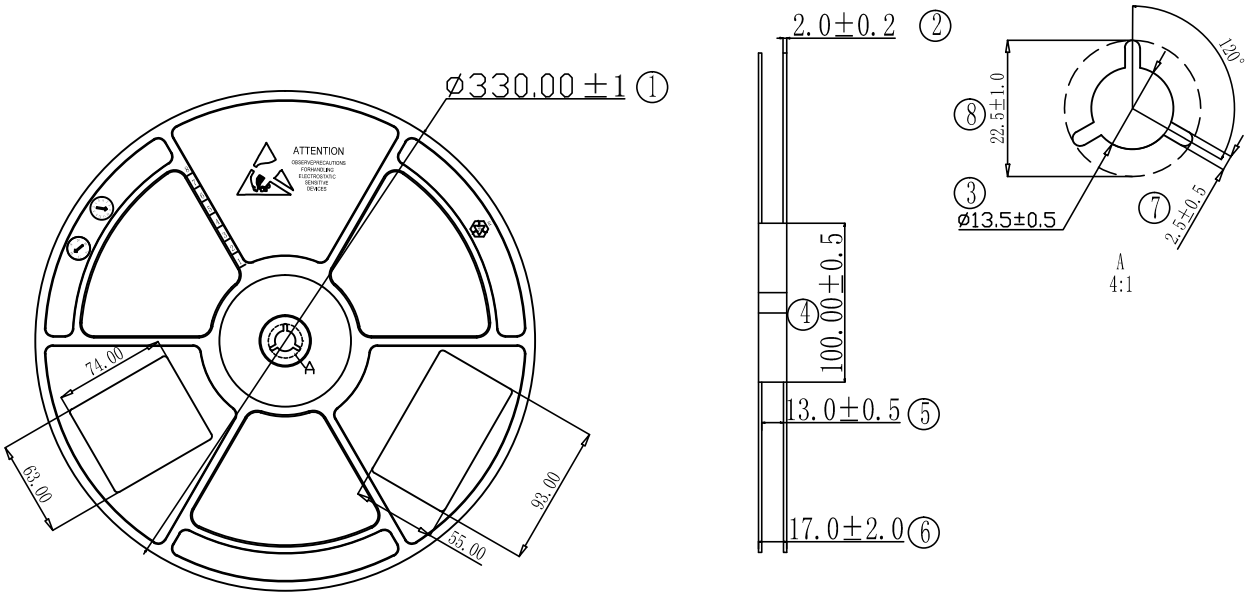

**Figure.10:** Maximum Effective Transient Thermal Impedance, Junction-to-Case

DFN5×6-8 Package Information：

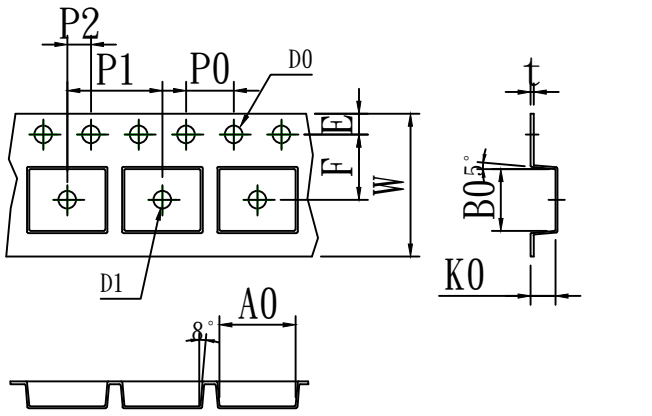


## Tape & Reel Information

Dimensions in mm




| Symbol | A0 | B0 | K0 | D0 | D1 | P0 | P1 | 10*P0 |
|---|---|---|---|---|---|---|---|---|
| Spec | 6.15±0.10 | 5.40±0.10 | 1.30±0.10 | 1.55±0.10 | 1.55±0.10 | 4.00±0.10 | 8.00±0.10 | 40.00±0.10 |
| Symbol | W | E | F | P2 | t | | | |
| Spec | 12.00±0.10 | 1.75±0.10 | 5.50±0.10 | 2.00±0.10 | 0.20±0.05 | | | |




Pulling direction

## Marking Information：

①. Doingter LOGO

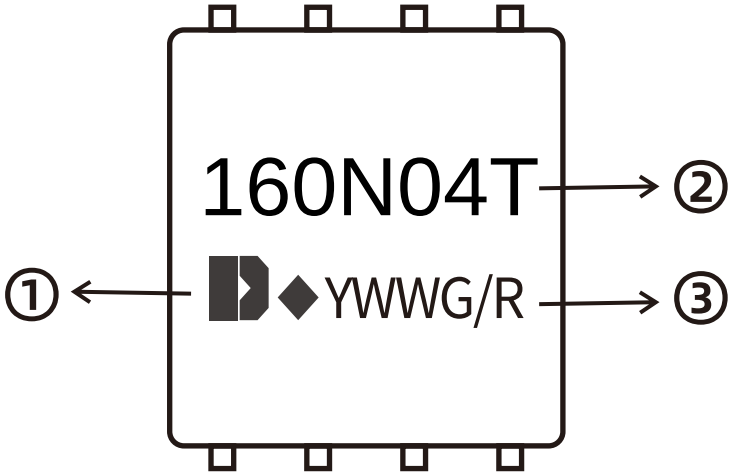
②. Part NO.

③. Date Code(YWWG / R)

Y：Year Code，last digit of the year

WW：Week Code(01-53)

G/R：G(Green) /R(Lead Free)




## Previous Version

| Version | Date | Subjects (major changes since last revision) |
|---|---|---|
| 1.0 | 2024-05-26 | Release of final version |

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